

## Dual P-Channel Enhancement Mode Power MOSFET

### General Description

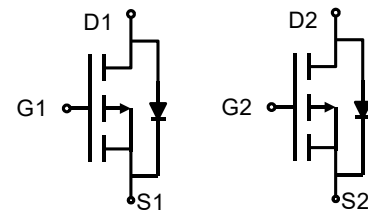
The G120P03S2 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge. It can be used in a wide variety of applications.

### Features

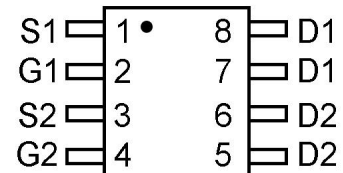
- $V_{DS}$  -30V
- $I_D$  (at  $V_{GS} = 10V$ ) -16A
- $R_{DS(ON)}$  (at  $V_{GS} = 10V$ ) < 14mΩ
- $R_{DS(ON)}$  (at  $V_{GS} = 4.5V$ ) < 18mΩ
- 100% Avalanche Tested
- RoHS Compliant

### Application

- DC-DC converter
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOP-8

Device	Package	Marking	Packaging
G120P03S2	SOP-8 Dual	G120P03	4000pcs/Reel

### Absolute Maximum Ratings $T_C = 25^\circ C$ , unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Continuous Drain Current	$I_D$	-16	A
Pulsed Drain Current (note1)	$I_{DM}$	-64	A
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Power Dissipation	$P_D$	1.4	W
Single pulse avalanche energy (note3)	$E_{AS}$	110	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 To 150	$^\circ C$

### Thermal Resistance

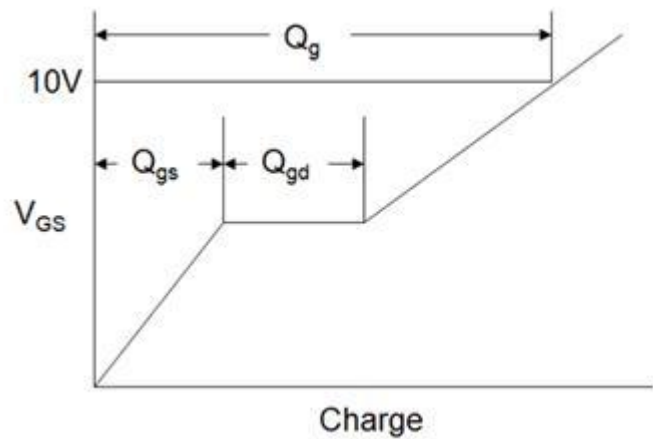
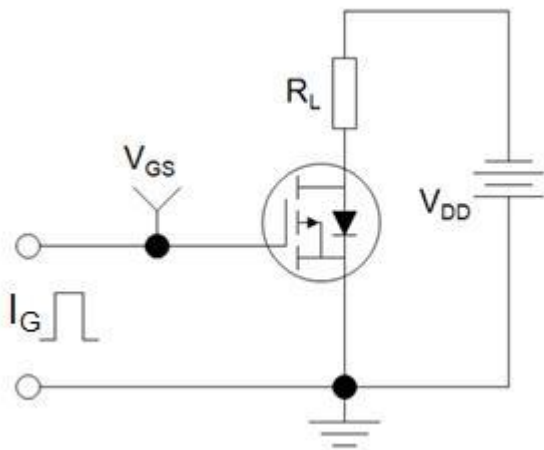
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	90	$^\circ C/W$

Specifications $T_J = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static Parameters</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -30V, V_{GS} = 0V$	--	--	-1	$\mu A$
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20V$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1	-1.5	-2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -10A$	--	11	14	m $\Omega$
		$V_{GS} = -4.5V, I_D = -7A$	--	15	18	
Forward Transconductance	$g_{FS}$	$V_{DS} = -5V, I_D = -10A$	--	23	--	S
<b>Dynamic Parameters</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = -15V,$ $f = 1.0MHz$	--	2835	--	pF
Output Capacitance	$C_{oss}$		--	333	--	
Reverse Transfer Capacitance	$C_{rss}$		--	324	--	
Total Gate Charge	$Q_g$	$V_{DD} = -15V,$ $I_D = -10A,$ $V_{GS} = -10V$	--	35	--	nC
Gate-Source Charge	$Q_{gs}$		--	5.7	--	
Gate-Drain Charge	$Q_{gd}$		--	8.8	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -15V,$ $I_D = -10A,$ $R_G = 1\Omega$	--	11	--	ns
Turn-on Rise Time	$t_r$		--	7.5	--	
Turn-off Delay Time	$t_{d(off)}$		--	43.5	--	
Turn-off Fall Time	$t_f$		--	17.5	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	--	--	-16	A
Body Diode Voltage	$V_{SD}$	$T_J = 25^\circ\text{C}, I_{SD} = -10A, V_{GS} = 0V$	--	--	-1.2	V
Reverse Recovery Charge	$Q_{rr}$	$I_F = -10A, V_{GS} = 0V$ $di/dt = -100A/\mu s$	--	30	--	nC
Reverse Recovery Time	$T_{rr}$		--	22	--	ns

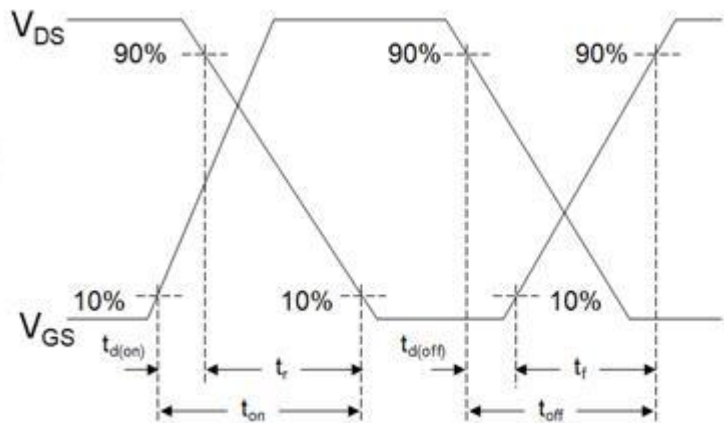
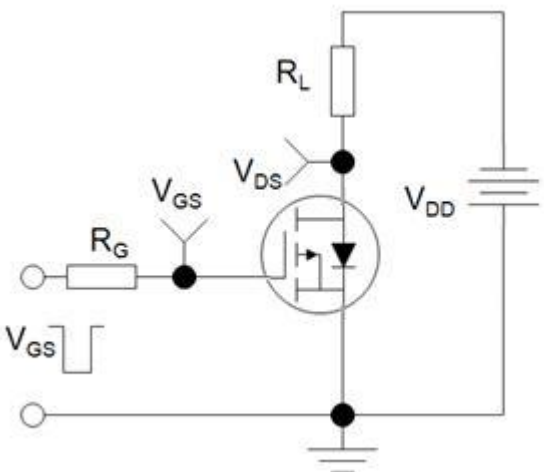
**Notes**

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical  $R_G$
3. EAS condition :  $T_J = 25^\circ\text{C}, V_{DD} = -30V, V_{GS} = -10V, L = 0.5mH, R_G = 25\Omega$

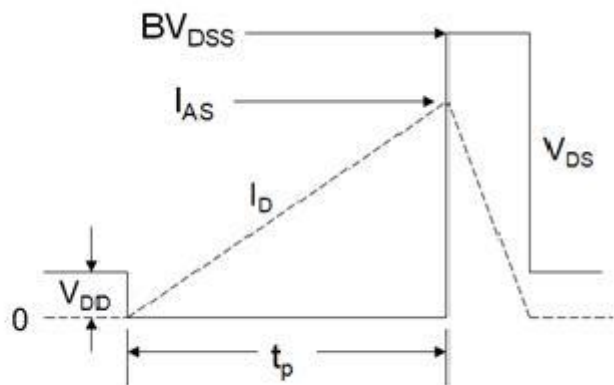
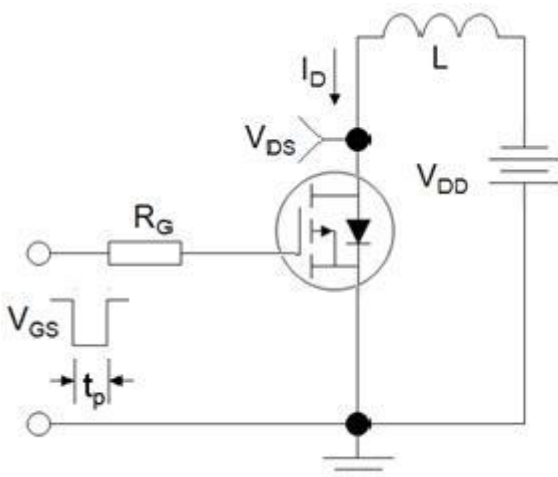
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 1. Output Characteristics

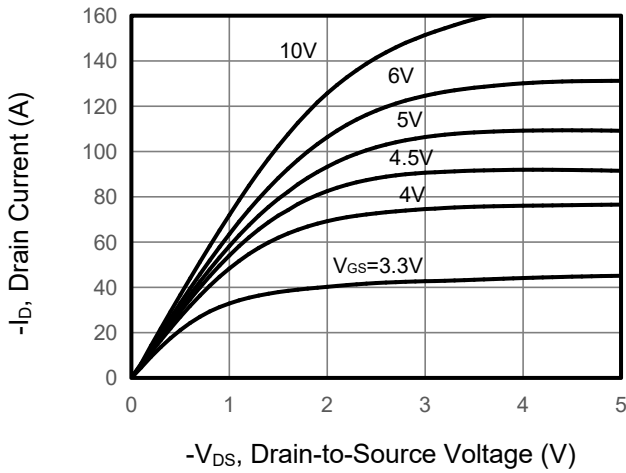


Figure 2. Transfer Characteristics

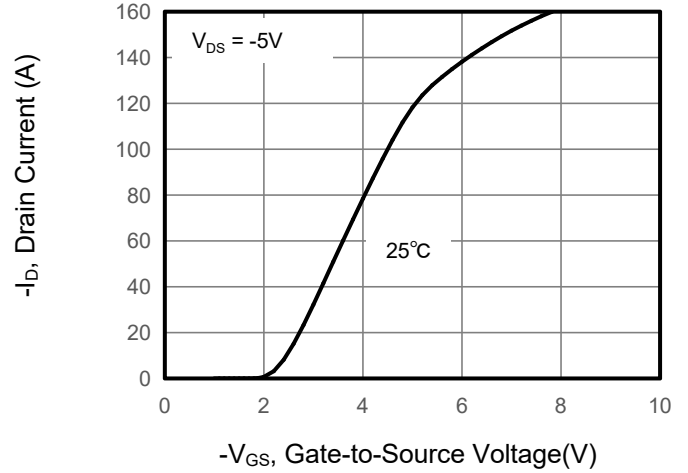


Figure 3. Drain Source On Resistance

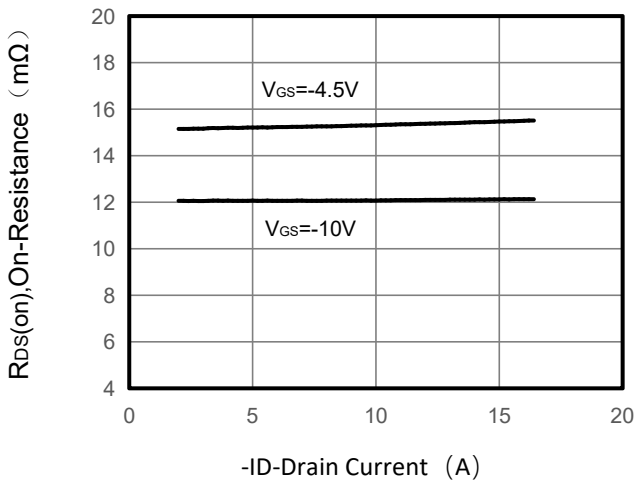


Figure 4. Gate Charge

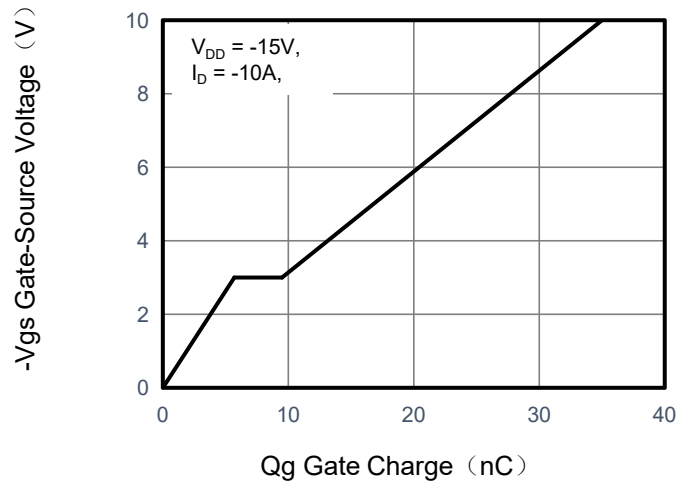


Figure 5. Capacitance

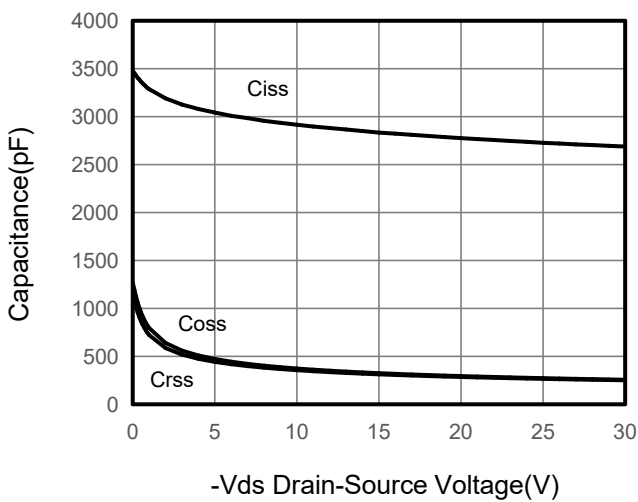
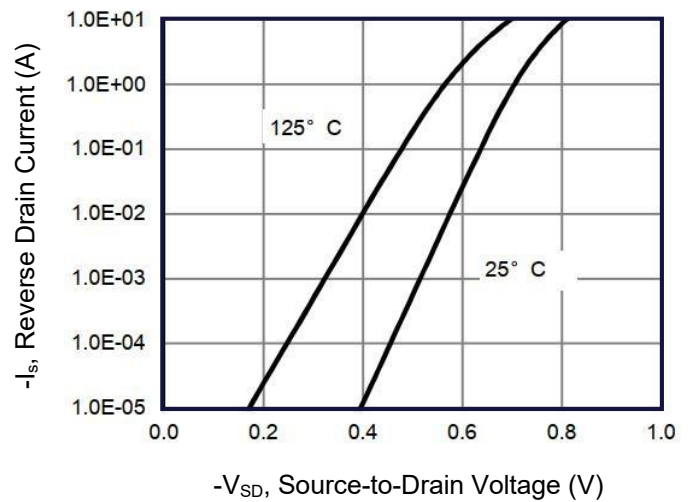


Figure 6. Source-Drain Diode Forward



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 7. Drain-Source On-Resistance

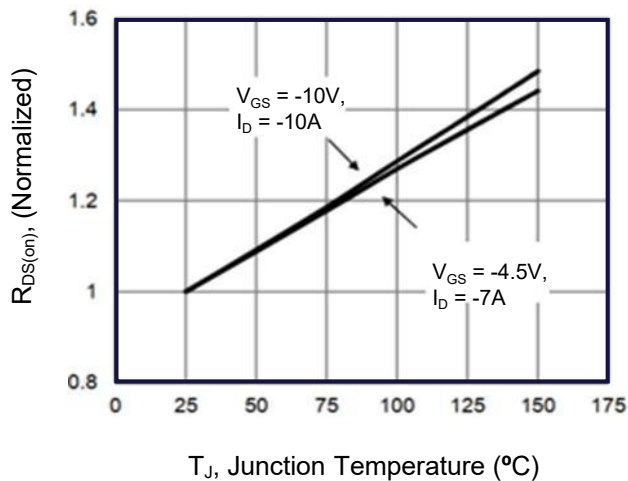


Figure 10. Safe Operation Area

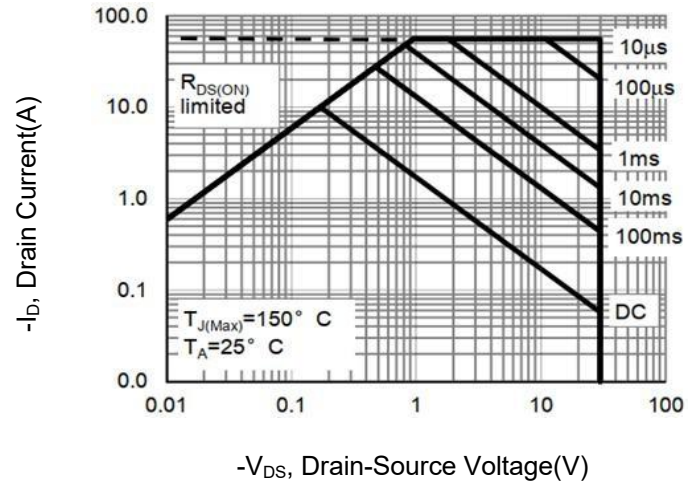
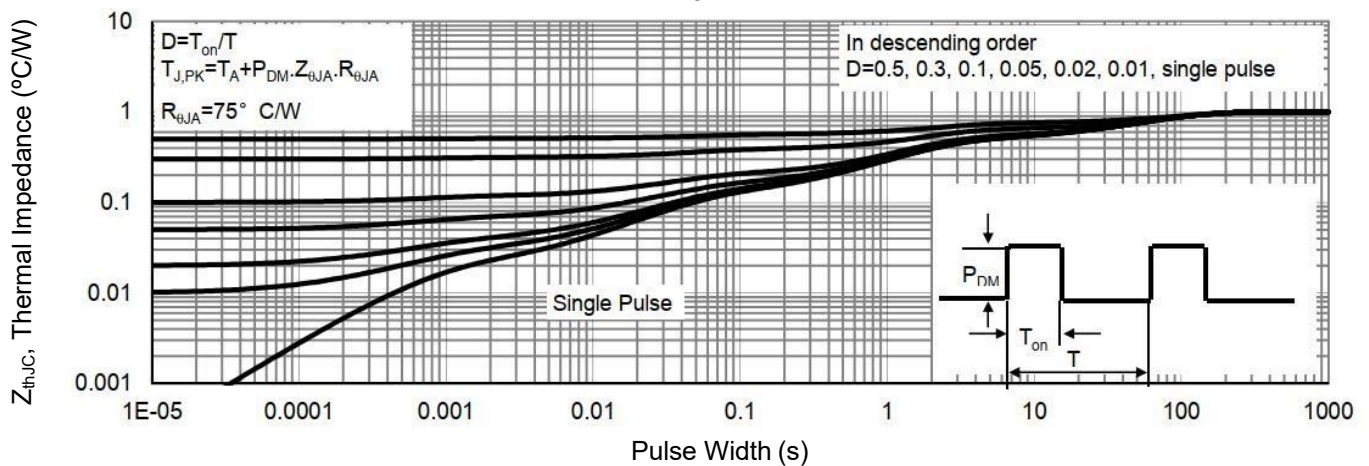
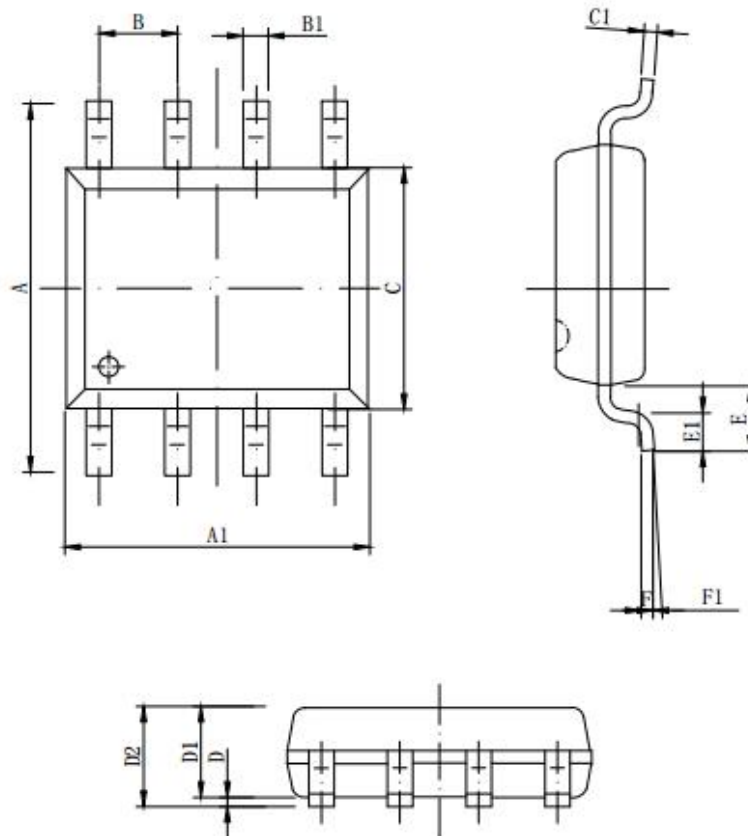


Figure 9. Normalized Maximum Transient Thermal Impedance



**SOP-8 Package Information**



Symbol	Dimensions in Millimeters		
	MIN.	NOM.	MAX.
A	5.800	6.000	6.200
A1	4.800	4.900	5.000
B	1.270BSC		
B1	0.35 <sup>8x</sup>	0.40 <sup>8x</sup>	0.45 <sup>8x</sup>
C	3.780	3.880	3.980
C1	--	0.203	0.253
D	0.050	0.150	0.250
D1	1.350	1.450	1.550
D2	1.500	1.600	1.700
D2	1.500	1.600	1.700
E	1.060REF		
E1	0.400	0.700	0.100
F	0.250BSC		
F1	2°	4°	6°

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [MOSFET](#) category:*

*Click to view products by [GOFORD](#) manufacturer:*

Other Similar products are found below :

[IRFD120](#) [JANTX2N5237](#) [BUK455-60A/B](#) [MIC4420CM-TR](#) [VN1206L](#) [NDP4060](#) [SI4482DY](#) [IPS70R2K0CEAKMA1](#) [SQD23N06-31L-GE3](#)  
[TK16J60W,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#) [DMN1053UCP4-7](#) [SQJ469EP-T1-GE3](#) [NTE2384](#) [DMC2700UDMQ-7](#)  
[DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [DMP22D4UFO-7B](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)  
[STF5N65M6](#) [IRF40H233XTMA1](#) [STU5N65M6](#) [DMN6022SSD-13](#) [DMN13M9UCA6-7](#) [DMTH10H4M6SPS-13](#) [DMN2990UFB-7B](#)  
[IPB80P04P405ATMA2](#) [2N7002W-G](#) [MCAC30N06Y-TP](#) [MCQ7328-TP](#) [NTMC083NP10M5L](#) [BXP7N65D](#) [BXP4N65F](#) [AOL1454G](#)  
[WMJ80N60C4](#) [BXP2N20L](#) [BXP2N65D](#) [BXT1150N10J](#) [BXT1700P06M](#) [TSM60NB380CP](#) [ROG](#) [RQ7L055BGTGR](#) [DMNH15H110SK3-13](#)  
[SLF10N65ABV2](#) [BSO203SP](#) [BSO211P](#) [IPA60R230P6](#)